


☒ Saved

- S34: (6331) ((fer\$10 "FeRAM") near3 capacitor)
- S35: (6331) ((fer\$10 "FeRAM") near3 capacitor) S34 and (electrode plate)
- S36: (3545) S35 and dielectric
- S37: (1534) S36 and barrier
- S38: (1155) S37 and oxygen
- S39: (201) S38 and (seed liner lining)
- S40: (197) S39 and ((top bottom first second lower upper) near4 (electrode plate))
- S41: (133) S40 and ((top bottom first second lower upper) near4 (barrier))
- S42: (65) S41 and (glue adhes\$4)
- S43: (0) "10482280"
- S44: (1) "10482280"

 Favorites

Search	File	Remove	Advanced	Clear
DBs	NIS-PPUB; USPAT; EPO; JPO			
Default operator: FOR				
<input checked="" type="checkbox"/> Durals <input checked="" type="checkbox"/> Highlight all the items initially				
<div style="border: 1px solid black; height: 600px; padding: 10px;"> <p>"20010019141"</p> </div>				
RRS form	ISAR form	Insert	Text	HTML

	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	4	5
1		US 2001001	2001090	40	Semiconductor device with	257/295	257/306;		Takahashi, Seiichi							

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L11	1	(first adj barrier and second adj barrier and spacer and capacitor and buffer and plug).clm.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/08/24 17:23